

**Model Question Paper- I**  
**Fifth Semester B.E Degree**

**Course Title: Digital VLSI Design**

**Course Code: BVL503**

Duration: 03Hours

Max.Marks:100

Note: Answer any FIVE full questions, choosing at least ONE question from each Unit.

Q.No.	Module-1		M
1.	a)	With neat diagram <b>explain</b> the MOS Transistor physical Structure?	6
	b)	With neat diagram <b>explain</b> the simple CMOS flip flop with 2 mux and 2 inverters.	8
	c)	<b>Differentiate</b> between CMOS and NMOS	6
OR			
2.	a)	With neat diagram <b>explain</b> physical construction/ layout of CMOS flip-flop.	10
	b)	<b>Explain</b> how mos transistor can be used as switch?	10
Module-2			
3.	a)	<b>Write</b> the CMOS inverter circuit and briefly <b>explain</b> . Write the CMOS VTC showing regions A,B,C,D,E. <b>Derive</b> the expressions for output voltage in region D	10
	b)	<b>Explain</b> Accumulation, Depletion, and Inversion modes in an mos structure	6
	c)	With the circuit diagram <b>explain</b> CMOS tristate inverter.	4
OR			
4.	a)	<b>Explain</b> the n mos device behaviour under the influence of different terminal voltages with neat diagram.	8
	b)	<b>Explain</b> the following <ul style="list-style-type: none"> <li>i. channel length modulation</li> <li>ii. Noise margin</li> <li>iii. Body effect</li> </ul>	12

<b>Module-3</b>			
5.	a)	With a diagram <b>derive</b> an expression for sheet resistance. Also <b>write</b> the resistance of non-rectangular shapes	8
	b)	<b>Derive</b> an equation for resistance for rise and fall time w.r.t cmos inverter	8
	c)	<b>Explain</b> rise time, fall time, delay time with respect to switching characteristics for CMOS inverter.	4
<b>OR</b>			
6.	a)	<b>Explain</b> how long wire is represented in terms of distributed RC section and estimate the propagation time With suitable equation	4
	b)	<b>Derive</b> an equation for static and dynamic power dissipation w.r.t cmos inverter	8
	c)	<b>Write</b> a short note on i. Diffusion capacitance ii. Routing capacitance	8
<b>Module-4</b>			
7.	a)	<b>Realize</b> CMOS logic structure\ CMOS Complementary logic for Boolean expression $Z = \overline{AB + C(D + E)}$	6
	b)	<b>Explain</b> the C <sup>2</sup> MOS [clocked CMOS logic] with an example	6
	c)	<b>Explain</b> the circuit of pass logic function unit of a) NMOS b) Full CMOS TG	8
<b>OR</b>			
8.	a)	<b>Explain</b> Tri-state pad <b>and</b> Bi-directional with neat diagrams and truth table.	6
	b)	<b>Explain</b> the circuit of psudo NMOS logic by taking an example of the Boolean function $Y = \overline{AB + C(D + E)}$	6
	c)	<b>Explain</b> the dynamic version of CVSL with an example. Also realize 2 input AND/NAND using CVSL	8

<b>Module-5</b>			
9.	a)	<b>Explain</b> the CMOS SR Latch circuit based on NOR 2 input gates.	6
	b)	<b>Explain</b> the working of CMOS implementation of D-latch with neat circuit and timing diagram showing setup and hold time.	8
	c)	<b>Explain</b> the static behavior of the 2-inverter basic bistable element with neat circuit, schematic and voltage transfer curve	6
<b>OR</b>			
10.	a)	<b>Draw</b> the diagram of 4-bit x 4-bit NOR based ROM array. <b>Explain</b> its functioning.	6
	b)	With necessary circuit diagram <b>explain</b> the operation of 3-transistor DRAM cell with pull-up and read/write circuitry and waveforms.	10
	c)	<b>Explain</b> the operation of 1-transistor DRAM cell with its access lines	4